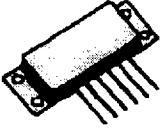
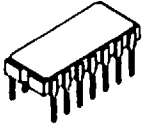


NEW ENGLAND SEMICONDUCTOR

POWER MOSFETS N CHANNEL DUAL

PACKAGE	DEVICE TYPE	BV _{DSS} VOLTS	I _D AMPS	R _{DS(on)} @0.5 I _D OHMS	Q _g nc	C _{ISS} pf	P _D WATTS
6 PIN SIP 	NFD600	600	11.0	0.6	105	1880	125
	NFD500	500	14.0	0.4	105	1880	125
	NFD460	500	20.0	0.25	130	2950	125
	NFD410	400	20.0	0.2	130	2950	125
	NFD400	400	17.0	0.3	105	1800	125
	NFD310	350	22.0	0.2	130	2950	125
	NFD300	350	17.0	0.3	105	1800	125
	NFD200	200	30.0	0.09	140	3000	125
	NFD100	100	30.0	0.06	120	3000	125

N CHANNEL QUAD

PACKAGE	DEVICE TYPE	BV _{DSS} VOLTS	I _D AMPS	R _{DS(on)} @0.5 I _D OHMS	VGS(th) min/max VOLTS	C _{ISS} pf	P _D WATTS
14 PIN QUAD DUAL IN LINE 	NSQ6659	35	0.85	5.0	0.8/2.5	50	1.3
	NSQ6660	60	0.46	5.0	0.8/2.5	50	1.3
	NSQ6661	90	0.4	5.3	0.8/2.5	50	1.3
	NSQ1000	60	0.225	5.5	0.8/2.5	60	1.3
	NSQ1001	30	0.85	1.0	0.8/2.5	110	1.3
	NSQ1004	60	0.46	3.5	0.8/2.5	60	1.3
	NSQ1006	90	0.4	4.5	0.8/2.5	60	1.3

- Electrical Characteristics @ 25° C unless otherwise noted
- Operational Temperature range: -55° to +150° C
- Storage temperature range: -55° to +150° C